

BC2101

P-Channel MOSFET

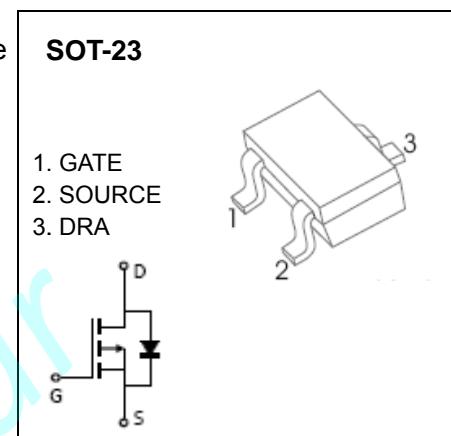
SOT-23 Plastic-Encapsulate MOSFETS

FEATURE

Leading Trench Technology for Low $R_{DS(on)}$ Extending Battery Life

APPLICATIONS

- High Side Load Switch
- Charging Circuit
- Single Cell Battery Applications such as Cell Phones, Digital Cameras ,PDAs, etc



MARKING: TS1

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	- 20	V
Gate-Source Voltage	V_{GS}	± 8.0	
Continuous Drain Current	I_D	-1.4	A
Pulsed Drain Current ($t_p=10\mu\text{s}$)	I_{DM}	-3.0	
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	431	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-50 ~+150	

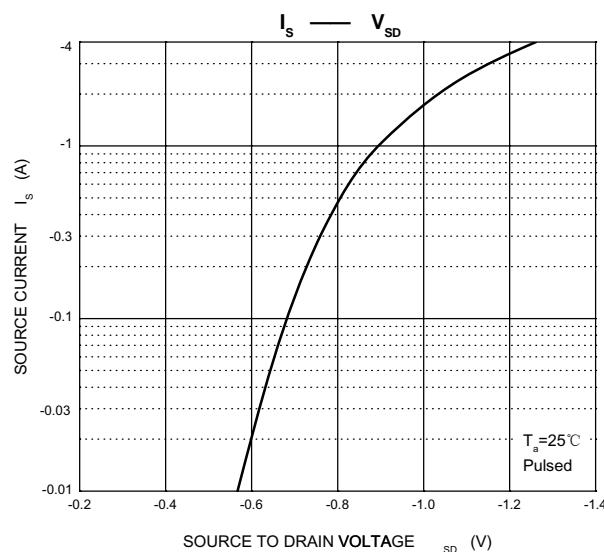
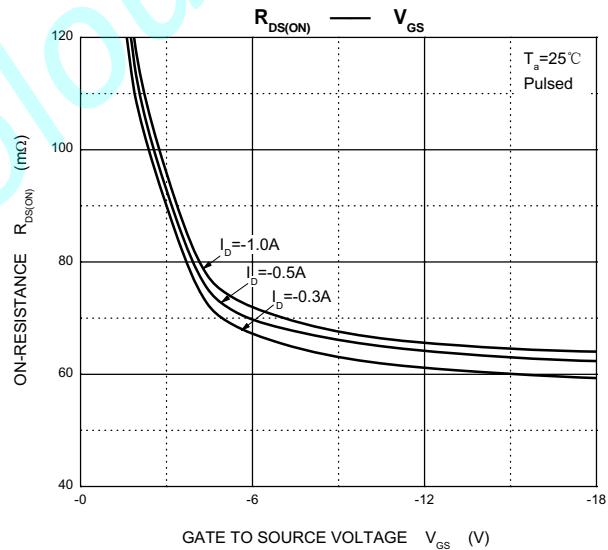
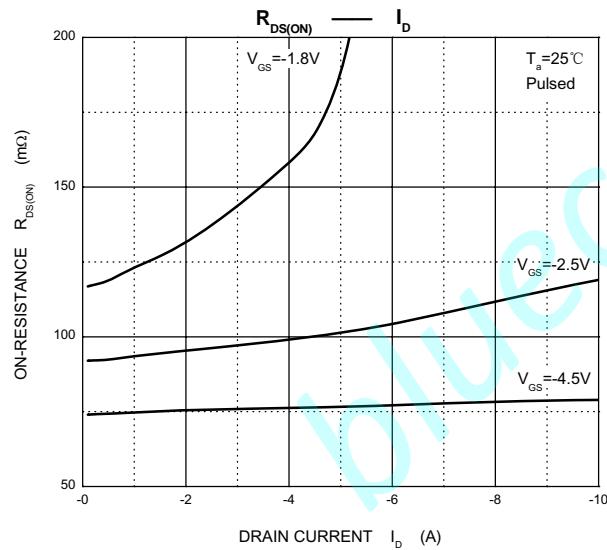
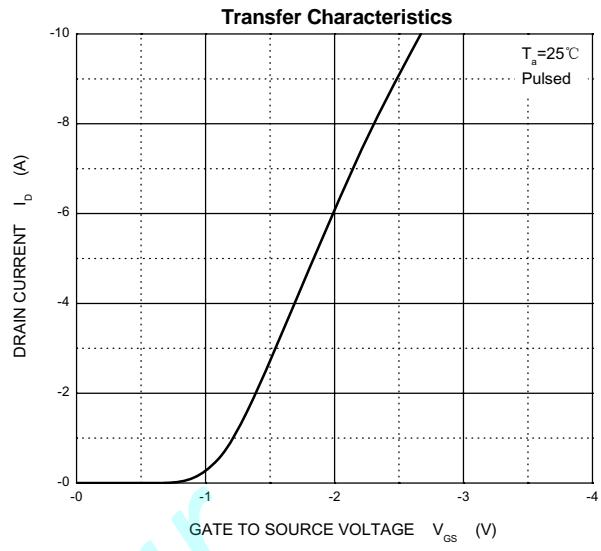
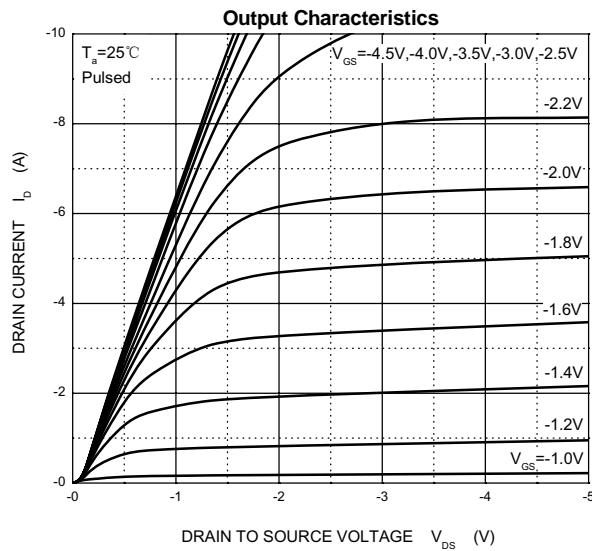
Electrical characteristics ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	V_{DSS}	$V_{GS} = 0V, I_D = -250\mu\text{A}$	-20			V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			± 100	nA
Zero Gate Voltage Drain Current	$I_{DS(on)}$	$V_{DS} = -20V, V_{GS} = 0V$			-1.0	μA
OFF CHARACTERISTICS (note 1)						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-0.45	-0.7		V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -1.0A$			100	$\text{m}\Omega$
		$V_{GS} = -2.5V, I_D = -0.5A$			140	
		$V_{GS} = -1.8V, I_D = -0.3A$			210	
CHARGES AND CAPACITANCES (note 3)						
Input Capacitance	C_{iss}	$V_{DS} = -8.0V, V_{GS} = 0V, f = 1\text{MHz}$		640		pF
Output Capacitance	C_{oss}			120		
Reverse Transfer Capacitance	C_{rss}			82		
SWITCHING CHARACTERISTICS (note 2,3)						
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = -4.5V, V_{DD} = -4.0V,$ $I_D = -1.0A, R_G = 6.2\Omega$		6.2		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(off)}$			26		
Fall Time	t_f			18		
Drain-source Body diode characteristics						
Forward Diode Voltage	V_{SD}	$V_{GS} = 0V, I_S = -0.3A$		-0.62	-1.2	V

Notes :

1. Pulse Test : pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
2. Switching characteristics are independent of operating junction temperatures.
3. These parameters have no way to verify.

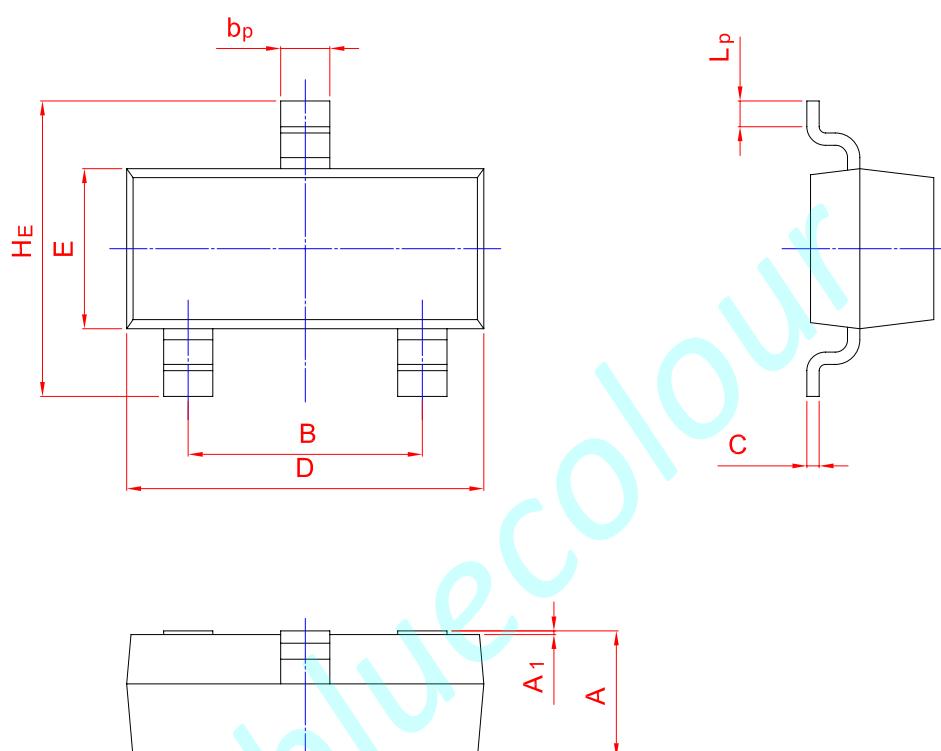
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b _p	C	D	E	H _E	A ₁	L _p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20